AiT Semiconductor Inc.

www.ait-ic.com

DESCRIPTION

The 2SB799 is available in the SOT-89 package.

APPLICATION

Switching and Amplifying in various electrical and electronic circuits.

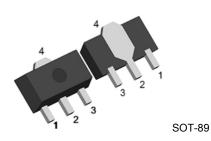
ORDERING INFORMATION

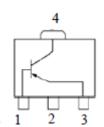
Package Type	Part Number		
SOT-89	2SB799		
SPQ 1,000pcs/Reel			
AiT provides all RoHS Compliant Products			

FEATURE

- Low Collector Saturation Voltage: V_{CE(SAT)} <-0.5V (I_C=-800mA, I_B=-80mA)
- Complements to NPN type 2SD1000

PIN DESCRIPTION





DESCRIPTION

PIN#	DESCRIPTION		
1	Base		
2,4	Collector		
3	Emitter		

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise specified.

,	
V _{CBO} , Collector-Base Voltage	-40 V
V _{CEO} , Collector-Emitter Voltage	-25 V
V _{EBO} , Emitter-Base Voltage	-6 V
Ic, Collector Current-Continuous	-1.5 A
P _{tot} , Total power dissipation (TA = 25 °C) ⁽¹⁾	-1 W
T _J , Junction Temperature	150 °C
T _{stg} , Storage Temperature	-55 ~ +150 °C

⁽¹⁾ Mounted on printed circuit board.

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

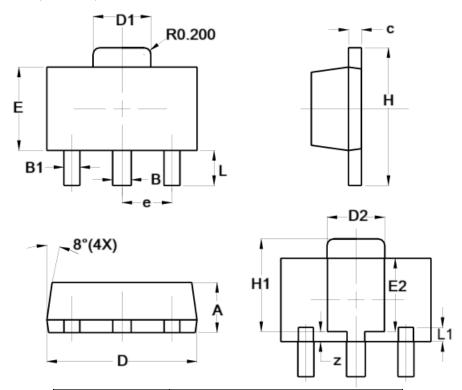
ELECTRICAL CHARACTERISTICS

 T_A =25°C unless otherwise specified.

Parameter	Symbols	Conditions	Min.	Тур.	Max.	Unit
Collector-Emitter Breakdown Voltage	V _(BR) CEO	$I_{C} = -2 \text{ mA}, I_{B} = 0$	-25	ı	ı	V
Collector-Base Breakdown Voltage	V _(BR) CBO	I _C = -100 μA, I _E = 0	-40	-	-	>
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E = -100 μA, I _C = 0	-6	1	1	>
Collector Cutoff Current	Ісво	V _{CB} = -35 V, I _E = 0	-	-	-100	nA
DC Current Gain	h _{FE}	V _{CE} = -1 V, I _C = -100 mA	200	-	300	-
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = -800 mA, I _B = -80 mA,	-	-	-0.5	V
Transition Frequency	f⊤	V _{CE} = 10 V, I _E = 50 mA f = 100 MHz	200	-	-	MHz

PACKAGE INFORMATION

Dimension in SOT-89 (Unit: mm)



Comple of	Millimeter			
Symbol	Min.	Max.		
Α	1.400	1.600		
В	0.500	0.620		
B1	0.420	0.540		
С	0.350	0.430		
D	4.440	4.600		
D1	1.620	1.830		
D2	1.610	1.810		
Е	2.400	2.600		
E2	2.050	2.350		
е	1.500 TYP.			
Н	3.950	4.250		
H1	2.630	2.930		
L	0.900	1.200		
L1	0.327 0.527			
Z	0.200	0.400		

2SB799 TRANSISTOR

PNP SILICON GENERAL PURPOSE TRANSISTOR

IMPORTANT NOTICE

AiT Semiconductor Inc. (AiT) reserves the right to make changes to any its product, specifications, to discontinue any integrated circuit product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

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AiT Semiconductor Inc. assumes to no liability to customer product design or application support. AiT warrants the performance of its products of the specifications applicable at the time of sale.

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